

PRM8R9N06D

PFC Device Corporation

60V Single N-Channel MOSFET

Major ratings and characteristics

Characteristics	Values	Units
V_{DS}	60	٧
$I_D^6 (T_C=25^{\circ}C)$	60	Α
Max. R _{DS(ON)} @V _{GS} =10V	8.9	mΩ
Max. R _{DS(ON)} @V _{GS} =4.5V	15	mΩ
T _J Operating Junction Temperature	-55 to +150	°C

General Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.

PRM8R9N06D TO-252 (D-PAK)

Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting

Features

- Max. $R_{DS(ON)}$ =8.9m Ω @ V_{GS} =10V
- Improved dv/dt capability
- Fast switching
- 100% E_{AS} Guaranteed
- Green Device Available

1. Characteristics

Maximum Ratings Characteristics

($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D^{5}	Drain Current – Continuous (T _C =25°C)	67	Α
ID	Drain Current – Continuous (T _C =100°C)	41	Α
I_D^6	Drain Current – Continuous (T _C =25°C)	60	А
I _{DM}	Drain Current – Pulsed ¹	240	А
E _{AS}	Single Pulse Avalanche Energy ²	16	mJ
I _{AS}	Single Pulse Avalanche Current ²	17	А
D	Power Dissipation (T _C =25°C)	62.5	W
P_D	Power Dissipation – Derate above 25°C	0.5	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction to ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction to Case		2	°C/W



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Electrical Characteristics

($T_J = 25$ °C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60			V
	Drain Source Leakage Current	V _{DS} =60V, V _{GS} =0V, T _J =25°C			1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =125°C			10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA

On Characteristics

ſ	R _{DS(ON)} Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A		7.2	8.9	mΩ	
	NDS(ON)		V _{GS} =4.5V, I _D =10A		11.4	15	mΩ
	$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=250uA$	1.0	1.6	2.5	V
ſ	g fs	Forward Transconductance	V _{DS} =5V, I _D =10A		30		S

Dynamic and switching Characteristics

Q_{g}	Total Gate Charge ^{3,4}	V _{DS} =30V, V _{GS} =10V, I _D =10A	 23.8	
Q_gs	Gate-Source Charge ^{3,4}		 4.2	 nC
Q_gd	Gate-Drain Charge ^{3, 4}		 4.6	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}	V_{DD} =30V, V_{GS} =10V, R_{G} =3 Ω	 11	
T _r	Turn-On Rise Time ^{3, 4}		 42	 ns
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}		 24	 113
T_f	Turn-Off Fall Time ^{3, 4}		 40	
C_{iss}	Input Capacitance		 1340	
C_{oss}	Output Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	 461	 pF
C_{rss}	Reverse Transfer Capacitance		 75	
R_{g}	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	 1.2	 Ω

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$V_{GS}=0V$, $I_{S}=20A$	 	1.5	V
t _{rr}	Reverse Recovery Time	1 204 4:/4+ 4004/	 21		ns
Q_{rr}	Reverse Recovery Charge	I _S =20A, di/dt=100A/us	 9		nC

Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. VDD=50V, VGS=10V, L=0.1mH, RG=25 Ω , Starting TJ=25 $^{\circ}$ C
- 3. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.
- 4. Essentially independent of operating temperature.
- 5. Silicon limited.
- 6. Package limited.

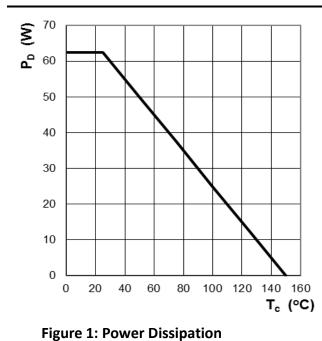


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2. Characteristics Curves

Ratings and Characteristics Curves

(T_A = 25°C unless otherwise specified)



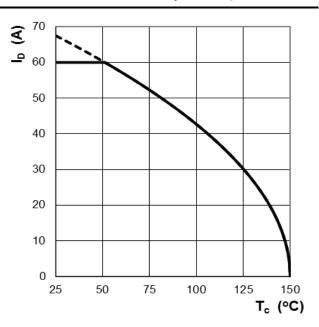


Figure 2: Continuous Drain Current vs. T_C

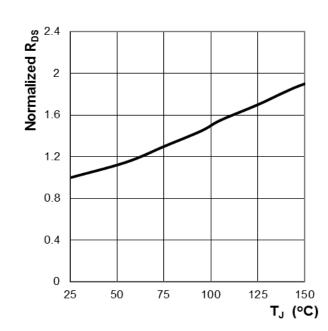


Figure 3: Normalized R_{DS(ON)} vs. T_J

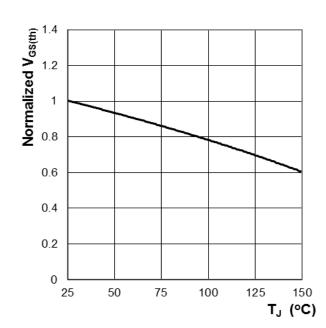


Figure 4: Normalized V_{GS(th)} vs. T_J



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Ratings and Characteristics Curves

($T_A = 25^{\circ}$ C unless otherwise specified)

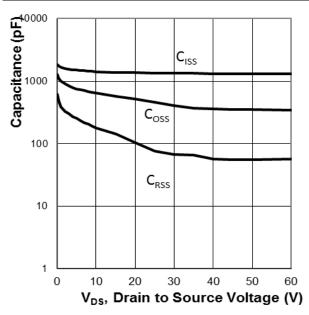


Figure 7: Typ. Capacitance Characteristics

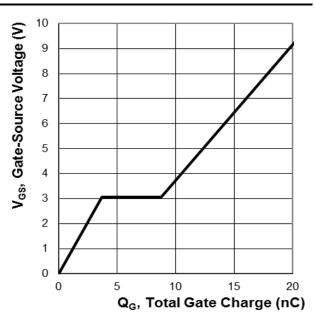


Figure 8: Typ. Gate Charge Characteristics

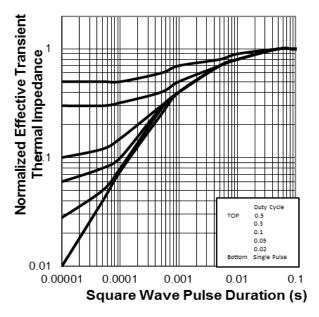


Figure 9: Normalized Thermal Transient Impedance, Junction-to-Case

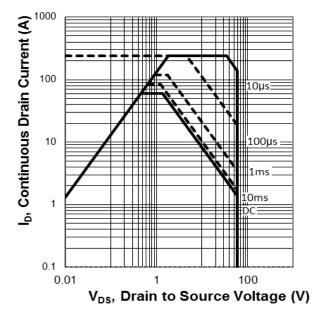


Figure 10: Maximum Safe Operation Area



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3. Marking information

Top Marking Rule

PFC PRM 8R9N06D YYWW ABSH PRM8R9N06D = Product Type Marking Code

YYWW = Date Code

YY = Last two digits of year

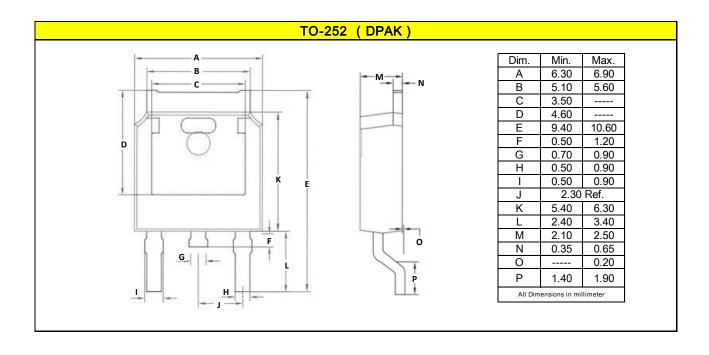
WW = Week code

ABS = Assembly code

H = Halogen Free (N/A = common molding compound)

4. Package information

Package Outline Dimensions millimeters





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5. Ordering information

Part Number	Package	Delivery mode
PRM8R9N06D	TO-252 (D-PAK)	2500 pcs / 13" diameter reel

Mechanical

Molder Plastic: UL Flammability Classification Rating 94V-0
 Device Weight: 0.01 ounces (0.3grams) - TO-252 (D-PAK)

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